

APR 18 2003

U.S. PATENT & TRADEMARK OFFICE

PATENT
Customer No. 22,852
Attorney Docket No. 04329.2335

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Tokuhisa OHIWA, et al.

Serial No.: 09/604,724

Filed: June 28, 2000

For: HIGH PRECISION PATTERN
FORMING METHOD OF
MANUFACTURING A
SEMICONDUCTOR DEVICE (AS
AMENDED)

)
)
) Group Art Unit: 2823
)
) Examiner: Maldonado, Julio J.

TECHNOLOGY CENTER 2800

APR 21 2003

RECEIVED

Assistant Commissioner for Patents
Washington, DC 20231

Sir:

AMENDMENT

In reply to the Office Action of January 31, 2003, with a period for response extending through April 30, 2003, Applicants amend the application as follows:

IN THE CLAIMS:

Please amend claims 1 and 21 as follows:

1. (Amended) A method of manufacturing a semiconductor device, comprising the steps of:

forming a soluble thin film by distributing and baking a coating solution on a film to be processed which is formed on a semiconductor substrate, wherein the soluble thin film is soluble in a dissolving liquid;

forming a mask layer on the soluble thin film;

forming a resist pattern on the mask layer;

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